Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO.	SERIAL NO.
LIST OF REFERENCES CITED BY APPLICANT		243707US2S DIV	~~New DIV Application~~ 10/680163
		APPLICANT: Mariko TAKAYANAGI	
		FILING DATE: ~~Herewith~~ 10/8/03	GROUP: ~~Not yet assigned~~ 2891

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,013,553	01/2000	WALLACE, ET AL.			
	AB	2002/0047141B1	04/2002	TERAMOTO			
	AC	6,303,481	10/2001	PARK			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	Yudong KIM, et al. "Conventional n-channel MOSFET devices using single layer HfO_2 and ZrO_2 as high-k gate dielectrics with polysilicon gate electrode", IEDM, 01-455, pgs. 455-458
	AX	
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner: [signature]

Date Considered: 5/16/05

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.